Data Sheet July 1999 File Number 2410.2

## 4.6A, 200V, 0.800 Ohm, N-Channel Power MOSFETs

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA9600.

## Ordering Information

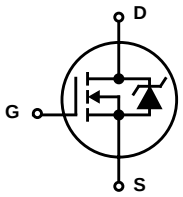
| PART NUMBER | PACKAGE | BRAND |
|---|---|---|
| IRFR220 | TO-252AA | IFR220 |
| IRFU220 | TO-251AA | IFU220 |

NOTE: When ordering, use the entire part number.

## Features

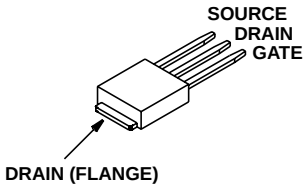
- 4.6A, 200V
- $r_{DS(ON)} = 0.800\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
  - TB334 “Guidelines for Soldering Surface Mount Components to PC Boards”

## Symbol

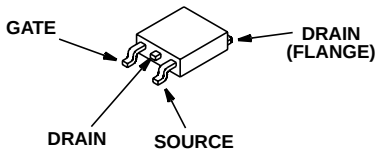



## Packaging

**JEDEC TO-251AA**




**JEDEC TO-252AA**



## Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specfied

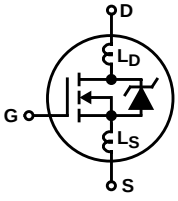
| | | IRFR220, IRFU220 | UNITS |
|---|---|---|---|
| Drain to Source Voltage (Note 1) | $V_{DS}$ | 200 | V |
| Drain to Gate Voltage ($R_{GS}$ = 20kΩ) (Note 1) | $V_{DGR}$ | 200 | V |
| Continuous Drain Current | $I_D$ | 4.6 | A |
| $T_C = 100^oC$ | $I_D$ | 2.9 | A |
| Pulsed Drain Current (Note 3) | $I_{DM}$ | 18 | A |
| Gate to Source Voltage | $V_{GS}$ | ±20 | V |
| Maximum Power Dissipation | $P_D$ | 50 | W |
| Linear Derating Factor | | 0.4 | $W/^oC$ |
| Single Pulse Avalanche Energy Rating (Note 4) | $E_{AS}$ | 85 | mJ |
| Operating and Storage Temperature | $T_J$, $T_{STG}$ | -55 to 150 | $^oC$ |
| Maximum Temperature for Soldering | | | |
| Leads at 0.063in (1.6mm) from Case for 10s | $T_L$ | 300 | $^oC$ |
| Package Body for 10s, See Techbrief 334 | $T_{pkg}$ | 260 | $^oC$ |

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

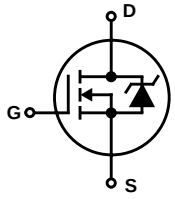
NOTE:

1. $T_J = 25^oC$ to $125^oC$.

## Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN | TYP | MAX | UNITS |
|---|---|---|---|---|---|---|---|
| Drain to Source Breakdown Voltage | $BV_{DSS}$ | $I_D$ = 250µA, $V_{GS}$ = 0V, (Figure 10) | | 200 | - | - | V |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}$, $I_D$ = 250µA | | 2.0 | - | 4.0 | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = Rated $BV_{DSS}$, $V_{GS}$ = 0V | | - | - | 25 | µA |
| | | $V_{DS}$ = 0.8 x Rated $BV_{DSS}$, $V_{GS}$ = 0V, $T_J = 125^oC$ | | - | - | 250 | µA |
| On-State Drain Current (Note 2) | $I_{D(ON)}$ | $V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}$, $V_{GS}$ = 10V, (Figure 7) | | 4.6 | - | - | A |
| Gate to Source Leakage Current | $I_{GSS}$ | $V_{GS}$ = ±20V | | - | - | ±100 | nA |
| Drain to Source On Resistance (Note 2) | $r_{DS(ON)}$ | $I_D$ = 2.4A, $V_{GS}$ = 10V, (Figures 8, 9) | | - | 0.47 | 0.800 | Ω |
| Forward Transconductance (Note 2) | $g_{fs}$ | $V_{DS} \geq 50V$, $I_D$ = 2.4A, (Figure 12) | | 1.7 | 2.6 | - | S |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{DD}$ = 100V, $I_D \approx$ 4.6A, $R_{GS}$ = 18Ω, $R_L$ = 18Ω, $V_{GS}$ = 10V<br>MOSFET Switching Times are Essentially Independent of Operating Temperature | | - | 8.8 | 13 | ns |
| Rise Time | $t_r$ | | | - | 27 | 41 | ns |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | - | 21 | 32 | ns |
| Fall Time | $t_f$ | | | - | 14 | 21 | ns |
| Total Gate Charge (Gate to Source + Gate to Drain) | $Q_{g(TOT)}$ | $V_{GS}$ = 10V, $I_D$ = 4.6A, $V_{DS}$ = 0.8 x Rated $BV_{DSS}$, $I_{g(REF)}$ = 1.5mA, (Figure 14)<br>Gate Charge is Essentially Independent of Operating Temperature | | - | 12 | 18 | nC |
| Gate to Source Charge | $Q_{gs}$ | | | - | 2.3 | 3.4 | nC |
| Gate to Drain "Miller" Charge | $Q_{gd}$ | | | - | 4.5 | 6.8 | nC |
| Input Capacitance | $C_{ISS}$ | $V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz, (Figure 11) | | - | 330 | - | pF |
| Output Capacitance | $C_{OSS}$ | | | - | 120 | - | pF |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | - | 41 | - | pF |
| Internal Drain Inductance | $L_D$ | Measured From the Drain Lead, 6.0mm (0.25in) From Package to Center of Die | Modified MOSFET Symbol Showing the Internal Device Inductances | - | 4.5 | - | nH |
| Internal Source Inductance | $L_S$ | Measured From the Source Lead, 6.0mm (0.25in) From Package to Source Bonding Pad |  | - | 7.5 | - | nH |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | | | - | - | 2.5 | $^oC/W$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | Typical Solder Mount | | - | - | 110 | $^oC/W$ |

## Source to Drain Diode Specifications

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|---|---|---|---|---|---|---|
| Continuous Source to Drain Current | $I_{SD}$ | Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Rectifier   | - | - | 4.6 | A |
| Pulse Source to Drain Current (Note 3) | $I_{SDM}$ | | - | - | 18 | A |
| Source to Drain Diode Voltage (Note 2) | $V_{SD}$ | $T_J = 25^oC$, $I_{SD} = 4.6A$, $V_{GS} = 0V$, (Figure 13) | - | - | 1.8 | V |
| Reverse Recovery Time | $t_{rr}$ | $T_J = 25^oC$, $I_{SD} = 4.6A$, $dI_{SD}/dt = 100A/\mu s$ | 69 | 170 | 400 | ns |
| Reverse Recovery Charge | $Q_{RR}$ | $T_J = 25^oC$, $I_{SD} = 4.6A$, $dI_{SD}/dt = 100A/\mu s$ | 0.30 | 0.72 | 1.8 | µC |

NOTES:

2. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.
3. Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
4. $V_{DD} = 10V$, starting $T_J = 25^oC$, L = 6.18mH, $R_G = 50\Omega$, peak $I_{AS} = 4.6A$.

## *Typical Performance Curves* Unless Otherwise Specified

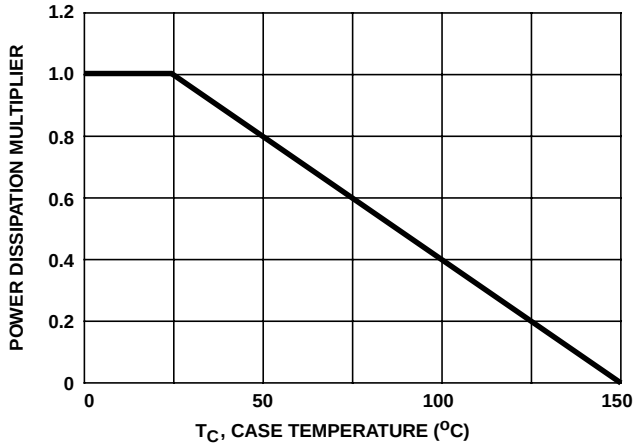



**FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE**

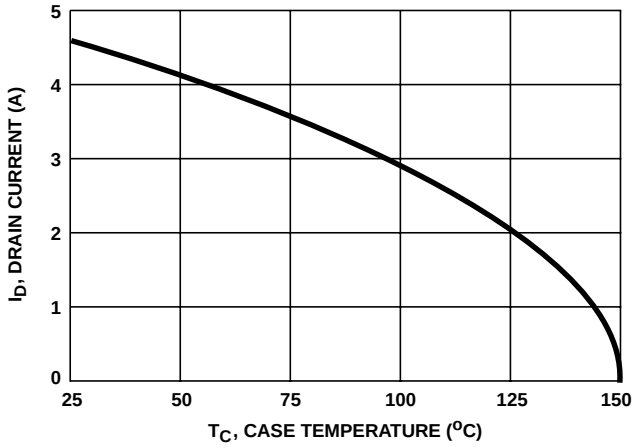



**FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE**

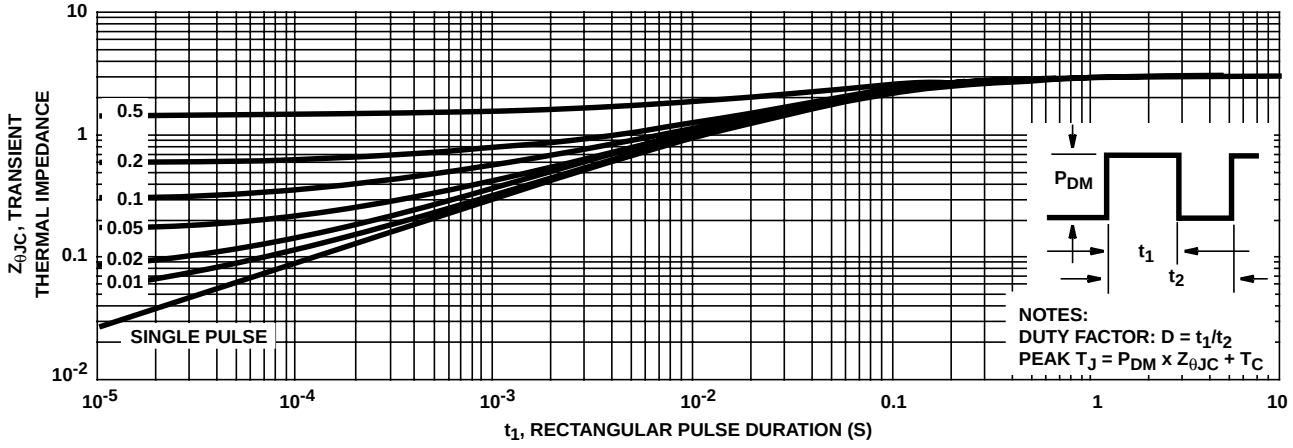



**FIGURE 3. MAXIMUM TRANSIENT THERMAL IMPEDANCE**

## Typical Performance Curves Unless Otherwise Specified (Continued)

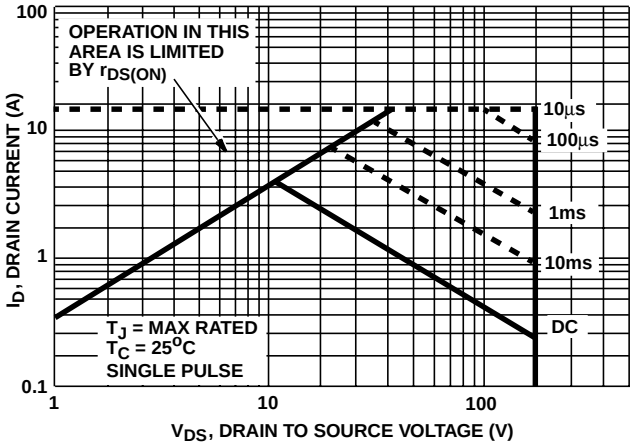



FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

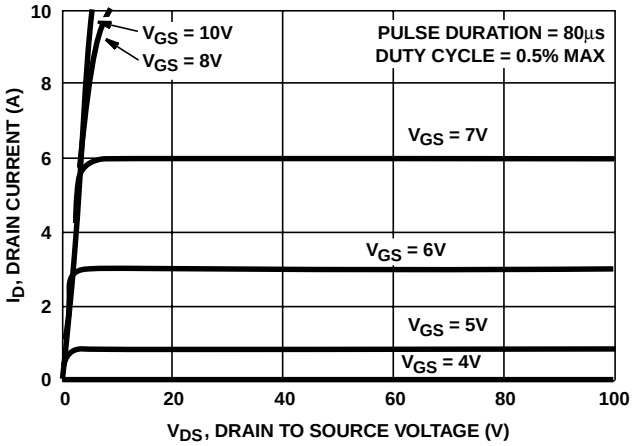



FIGURE 5. OUTPUT CHARACTERISTICS

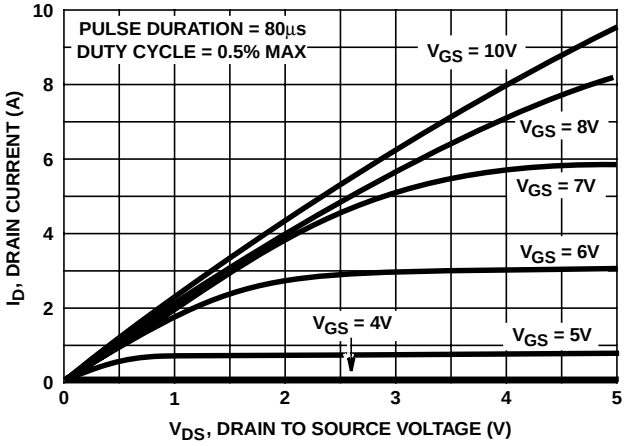



FIGURE 6. SATURATION CHARACTERISTICS

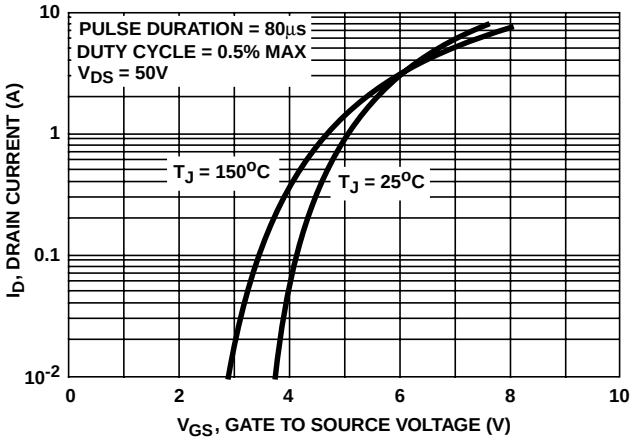



FIGURE 7. TRANSFER CHARACTERISTICS

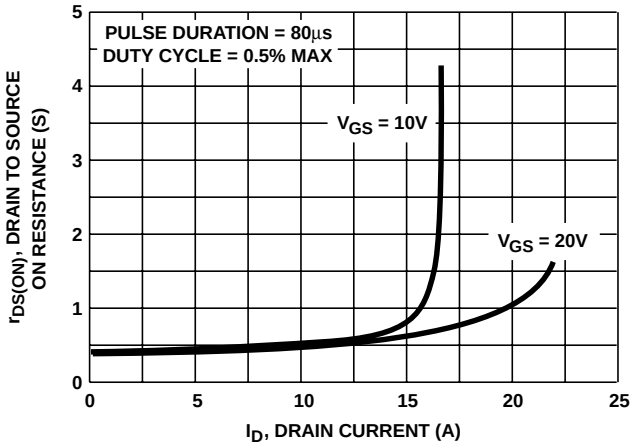



FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

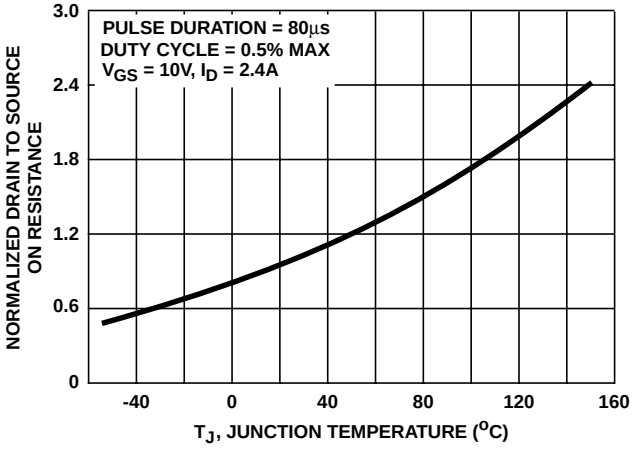



FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

## Typical Performance Curves Unless Otherwise Specified (Continued)

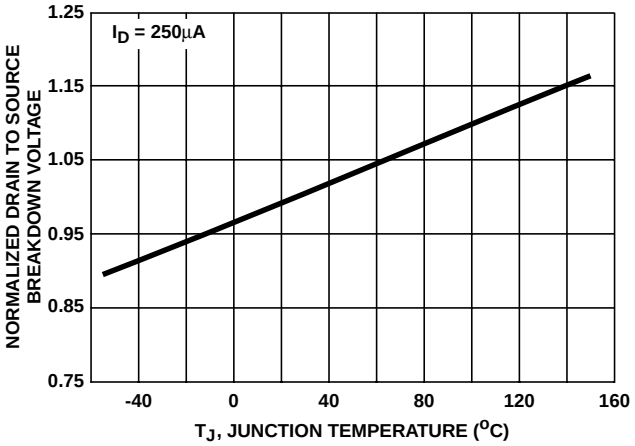



FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

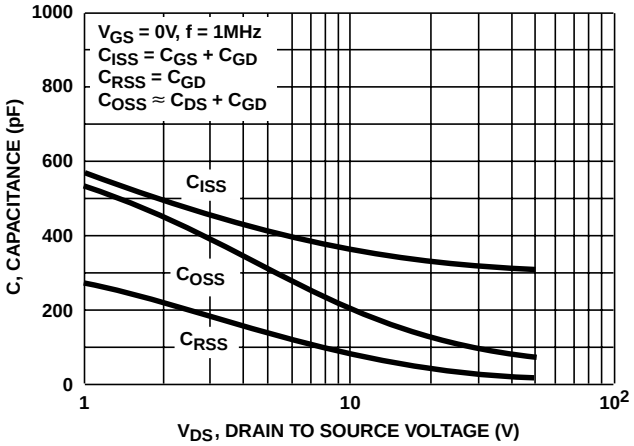



FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

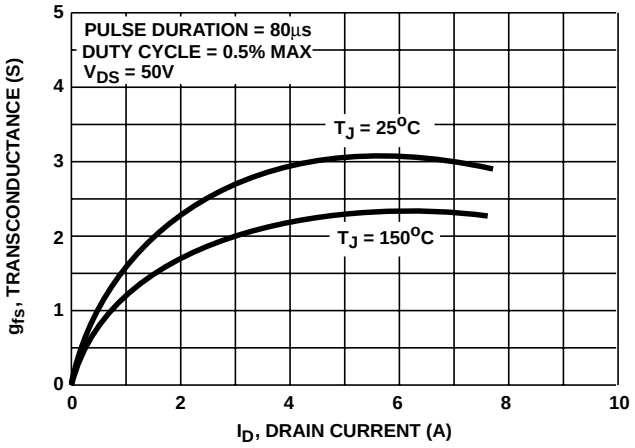



FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

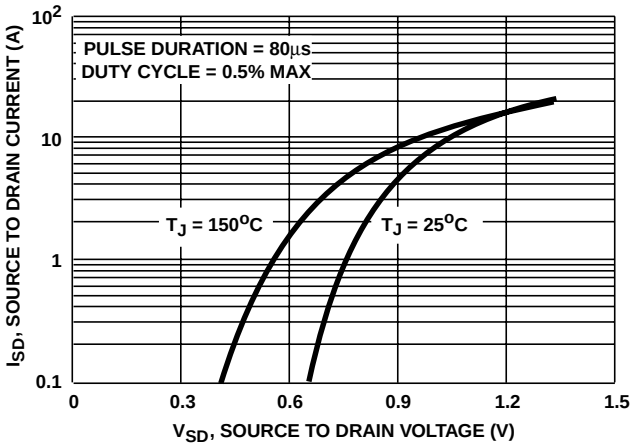



FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

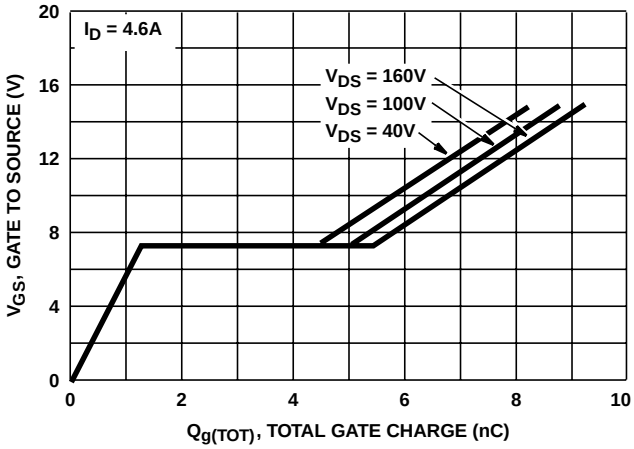



FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

## Test Circuits and Waveforms

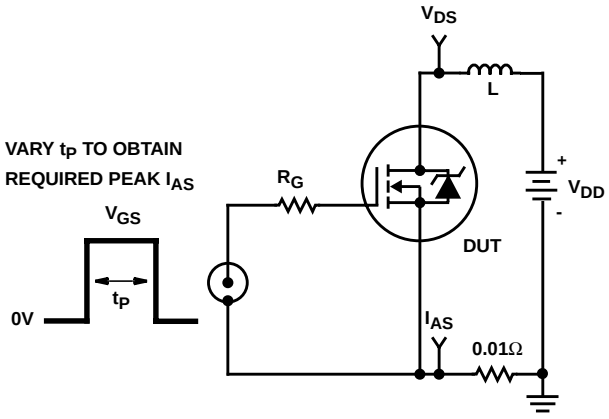



FIGURE 15. UNCLAMPED ENERGY TEST CIRCUIT

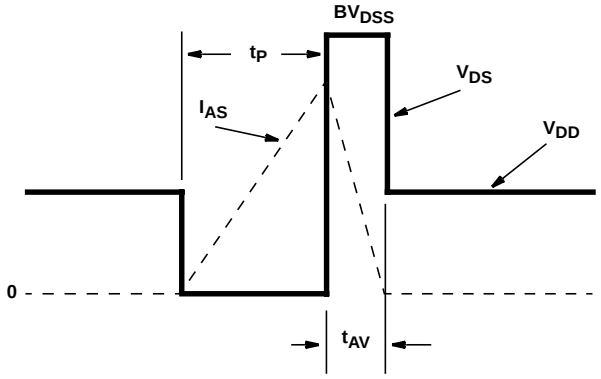



FIGURE 16. UNCLAMPED ENERGY WAVEFORMS

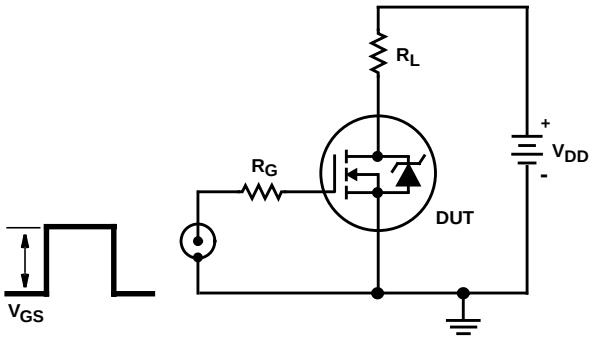



FIGURE 17. SWITCHING TIME TEST CIRCUIT

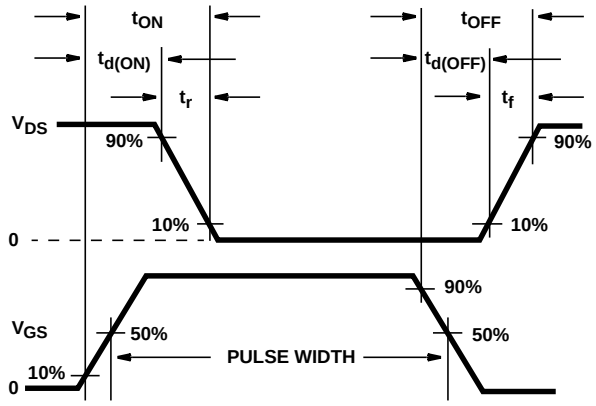



FIGURE 18. RESISTIVE SWITCHING WAVEFORMS

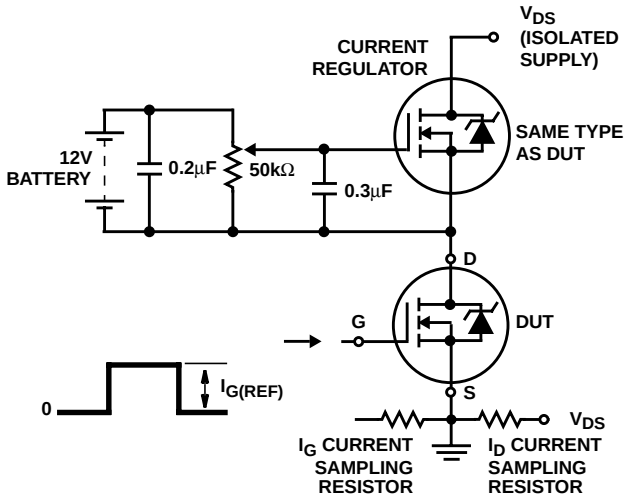



FIGURE 19. GATE CHARGE TEST CIRCUIT

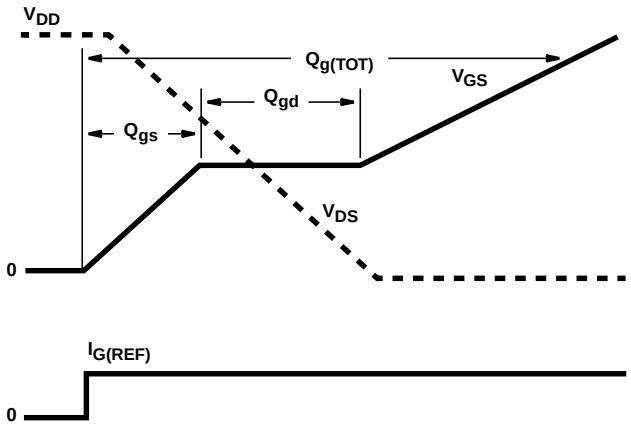



FIGURE 20. GATE CHARGE WAVEFORMS

## Sales Office Headquarters

**NORTH AMERICA**
Intersil Corporation
P. O. Box 883, Mail Stop 53-204
Melbourne, FL 32902
TEL: (407) 724-7000
FAX: (407) 724-7240

**EUROPE**
Intersil SA
Mercure Center
100, Rue de la Fusee
1130 Brussels, Belgium
TEL: (32) 2.724.2111
FAX: (32) 2.724.22.05

**ASIA**
Intersil (Taiwan) Ltd.
7F-6, No. 101 Fu Hsing North Road
Taipei, Taiwan
Republic of China
TEL: (886) 2 2716 9310
FAX: (886) 2 2715 3029